Ultra-Low 0.5Ω Dual SPDT Analog Switch

FEATURES

- Ultra−Low R_{ON} < 0.55Ω at V_{CC} = 4.3V
- V_{CC}: 1.65V to 5.5V
- Low Crosstalk
- Full 0 − V_{CC} Signal Handling Capability
- High Off−Channel Isolation
- Low Standby Current: <50nA
- Low Distortion
- R_{ONFLAT}: 0.15Ω Typical
- High Continuous Current Capability: ±300mA Through Each Switch
- ESD of Human Body Model: > ±4KV
- Packages: QFN10-1.8x1.4

APPLICATIONS

- Cell Phone Audio Block
- Speaker and Earphone Switching
- Ring-Tone Chip/Amplifier Switching
- Modems

GENERAL DESCRIPTIONS

The ASW5223 is an advanced CMOS analog switch fabricated in Sub-Micro Silicon gate CMOS technology. The device is a Dual Independent Single Pole Double Throw (SPDT) switch featuring Ultra-Low R_{ON} of 0.55Ω at V_{CC} = 4.3V.

The ASW5223 also features guaranteed Break-Before-Make (BBM) switching, assuring the switches never short the driver.

FUNCTION TABLE

IN1, IN2	NO1, NO2	NC1, NC2
0	OFF	ON
1	ON	OFF

BLOCK DIAGRAM

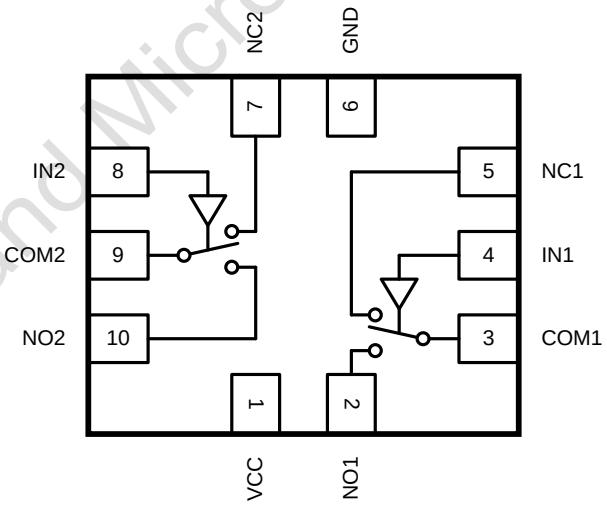

Figure 1, Block Diagram

PIN DIAGRAM

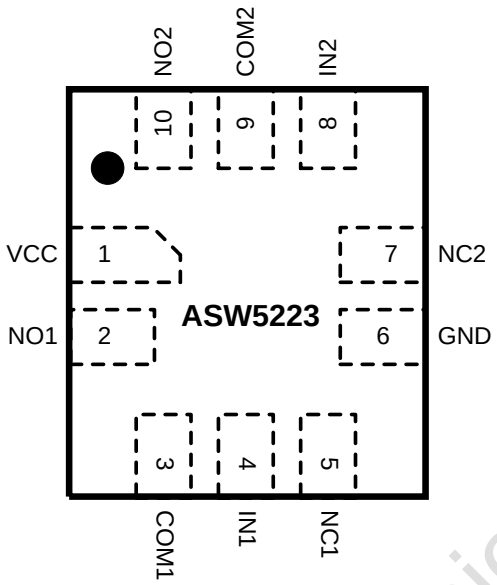

Figure 2, Pin Diagram (Top View)

PIN DESCRIPTIONS

PIN No.	PIN NAME	TYPE	DESCRIPTIONS
1	VCC	POWER	Power Supply Voltage
2	NO1	I/O	1-Side Data Path
3	COM1	I/O	1-Side Common Path
4	IN1	I	1-Side Input Control
5	NC1	I/O	1-Side Data Path
6	GND	GROUND	Ground
7	NC2	I/O	2-Side Data Path
8	IN2	I	2-Side Input Control
9	COM2	I/O	2-Side Common Path
10	NO2	I/O	2-Side Data Path